

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q83944

Hiroto OHTAKE, et al.

Appln. No.: Unknown

Confirmation No.: Unknown

Group Art Unit: Unknown

Filed: October 01, 2004

Examiner: Unknown

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD FOR THE SAME

INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. §§ 1.97 and 1.98

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

1. H. Hanahata et al., "Dependency of Basic Properties of Porous Silica ILD Thin Films in the k Range 1.6-2.7 on CMP Compatibility", Conference Proceedings ULSI XVI, 2001, Materials Research Society, page 629.
2. Japanese Laid-Open Patent Application Publication No. 2000-36484, published February 2, 2000.
3. Japanese Laid-Open Patent Application Publication No. 2001-35832, published February 9, 2001.

INFORMATION DISCLOSURE STATEMENT

New U.S. National Stage Application to Hiroto OHTAKE, et al.

4. Japanese Laid-Open Patent Application Publication No. 2000-269185, published September 29, 2000.
5. Japanese Laid-Open Patent Application Publication No. 2001-351976, published December 21, 2001.
6. Japanese Unexamined Patent Application Publication No. H07-193049, published July 28, 1995.
7. Japanese Laid-Open Patent Application Publication No. 2001-351897, published December 21, 2001.
8. Japanese Laid-Open Patent Application Publication No. 2000-114367, published April 21, 2000.
9. Japanese Unexamined Patent Application Publication No. H10-125783, published May 15, 1998.
- 10 Japanese Unexamined Patent Application Publication No. H11-297829, published October 29, 1999.
11. U.S. Patent No. 6,114,250, published September 5, 2000.
12. Japanese Laid-Open Patent Application Publication No. 2003-92287, published March 28, 2003.
13. Japanese Laid-Open Patent Application Publication No. 2002-110788, published April 12, 2002.

One copy of each of the listed documents is submitted herewith. Also enclosed is a copy of the International Search Report dated July 8, 2003, which cites references 8-13.

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date; (2) Before the mailing date of the first Office Action on the merits

INFORMATION DISCLOSURE STATEMENT

New U.S. National Stage Application to Hiroto OHTAKE, et al.

10/509898
DT09 Rec'd PCT/PTO 01 OCT 2004

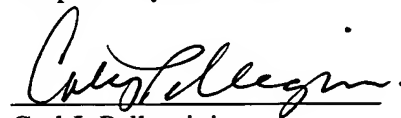
(whichever is later); or (3) Before the mailing date of the first Office Action after filing a request for continued examination (RCE) under §1.114, and therefore, no Statement under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant states that above references 2-7 are discussed within the specification beginning at page 2, line 17, page 3, line 11, page 4, lines 11 and 26, and page 5, lines 18 and 20, respectively.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account. A duplicate copy of this paper is attached.

Respectfully submitted,



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Date: October 1, 2004

Substitute for Form 1449 A & B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	Unknown
				Confirmation Number	Unknown
				Filing Date	October 01, 2004
				First Named Inventor	Hiroto OHTAKE
				Art Unit	Unknown
				Examiner Name	Unknown
Sheet	1	of	1	Attorney Docket Number	Q83944

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US 6,114,250	A	09-05-2000	Ellingboe et al.
		US			
		US			
		US			
		US			
		US			
		US			
		US			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
		JP	2000-36484	A	02-02-2000		No
		JP	2001-35832	A	02-09-2001		No
		JP	2000-269185	A	09-29-2000		No
		JP	2001-351976	A	12-21-2001		No
		JP	H07-193049	A	07-28-1995		No
		JP	2001-351897	A	12-21-2001		No
		JP	2000-114367	A	04-21-2000		No
		JP	H10-125783	A	05-15-1998		No
		JP	H11-297829	A	10-29-1999		No
		JP	2003-92287	A	03-28-2003		No
		JP	2002-110788	A	04-12-2002		No

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
		H. Hanahata et al., "Dependency of Basic Properties of Porous Silica ILD Thin Films in the k Range 1.6-2.7 on CMP Compatibility", Conference Proceedings ULSI XVI, 2001, Materials Research Society, page 629.	

Examiner Signature	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.